

FDS2572

150V, 0.047 Ohms, 4.9A, N-Channel UltraFET® Trench MOSFET

General Description

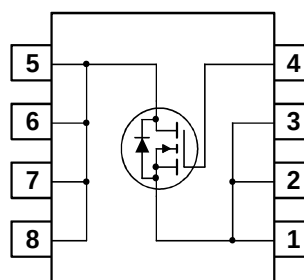
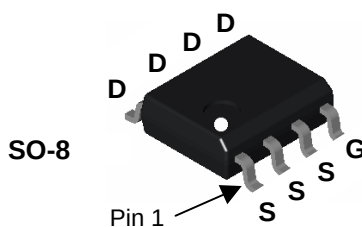
UltraFET® devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for $R_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Applications

- DC/DC converters
- Telecom and Data-Com Distributed Power Architectures
- 48-volt I/P Half-Bridge/Full-Bridge
- 24-volt Forward and Push-Pull topologies

Features

- $R_{DS(ON)} = 0.040\Omega$ (Typ.), $V_{GS} = 10V$
- $Q_{g(TOT)} = 29nC$ (Typ.), $V_{GS} = 10V$
- Low Q_{RR} Body Diode
- Maximized efficiency at high frequencies
- UIS Rated



MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ C$, $V_{GS} = 10V$, $R_{\theta JA} = 50^\circ C/W$)	4.9	A
	Continuous ($T_C = 100^\circ C$, $V_{GS} = 10V$, $R_{\theta JA} = 50^\circ C/W$)	3.1	A
	Pulsed	Figure 4	A
P_D	Power dissipation	2.5	W
	Derate above $25^\circ C$	20	mW/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ C$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	(NOTE1)	25	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Case at 10 seconds	(NOTE2)	50	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Case at steady state	(NOTE2)	85	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS2572	FDS2572	330mm	12mm	2500units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	150	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{V}$ $V_{GS} = 0\text{V}$ $T_C = 150^\circ$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 4.9\text{A}$, $V_{GS} = 10\text{V}$	-	0.040	0.047	Ω
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 4.9\text{A}$, $V_{GS} = 6\text{V}$	-	0.044	0.053	Ω

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	2050	-	pF
C_{OSS}	Output Capacitance		-	220	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	48	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V	-	29	38	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V}$ to 2V	-	4	6	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 75\text{V}$ $I_D = 4.9\text{A}$ $I_g = 1.0\text{mA}$	-	8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	6	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	4	-	nC

Switching Characteristics

t_{ON}	Turn-On Time	$V_{DD} = 75\text{V}$, $I_D = 4.9\text{A}$ $V_{GS} = 10\text{V}$, $R_G = 10\Omega$	-	-	27	ns
$t_{d(ON)}$	Turn-On Delay Time		-	14	-	ns
t_r	Rise Time		-	4	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	44	-	ns
t_f	Fall Time		-	22	-	ns
t_{OFF}	Turn-Off Time		-	-	100	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 4.9\text{A}$	-	-	1.25	V
		$I_{SD} = 3.1\text{A}$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 4.9\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	72	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 4.9$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	158	nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

2. $R_{\theta JA}$ is measured with 1.0in² copper on FR-4 board

Typical Characteristic

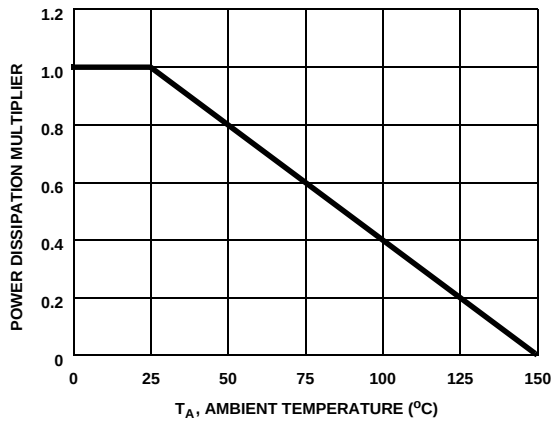


Figure 1. Normalized Power Dissipation vs Ambient Temperature

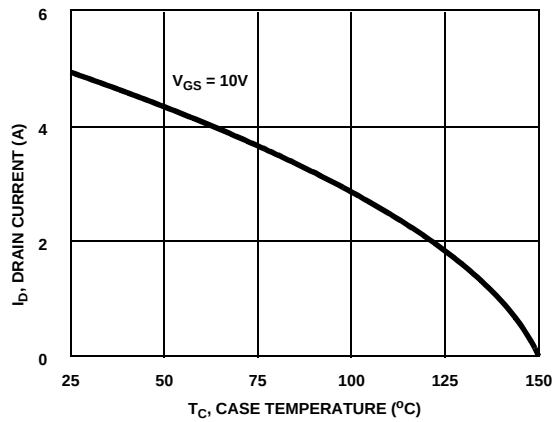


Figure 2. Maximum Continuous Drain Current vs Case Temperature

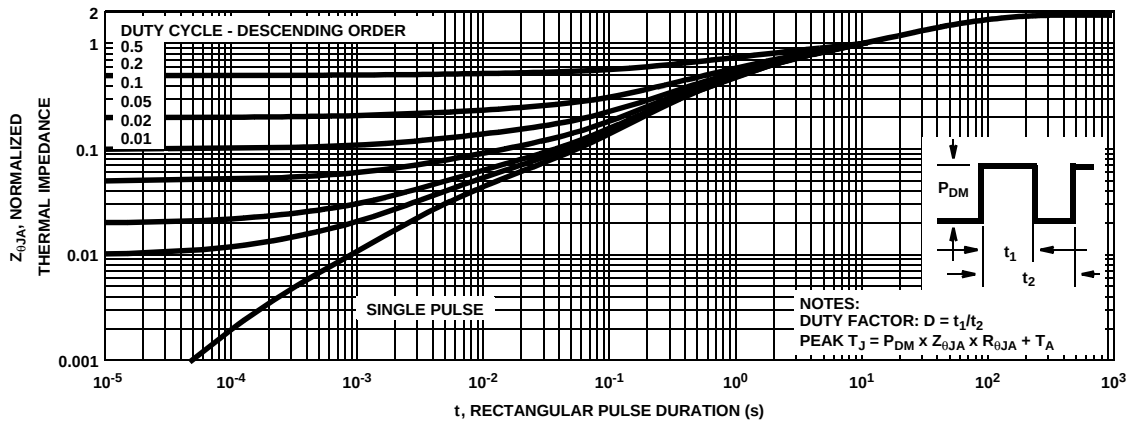


Figure 3. Normalized Maximum Transient Thermal Impedance

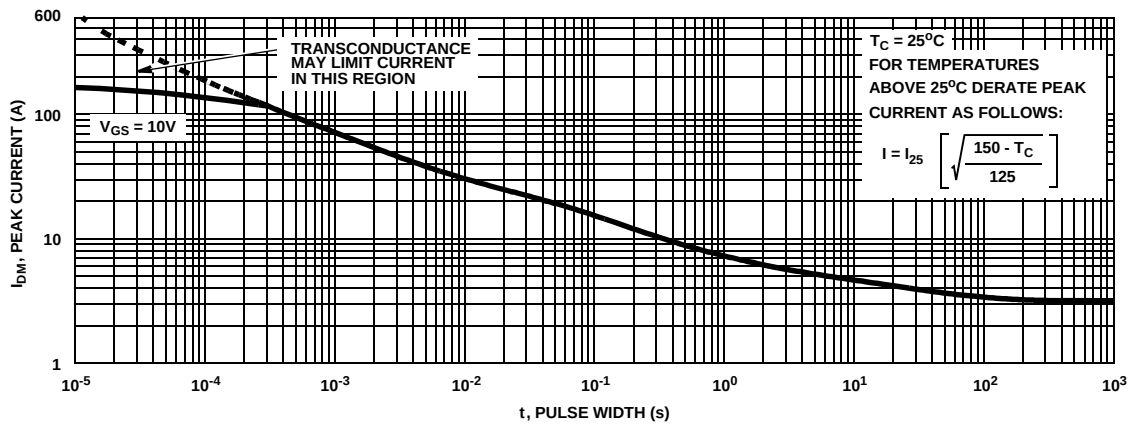


Figure 4. Peak Current Capability

Typical Characteristic (Continued)

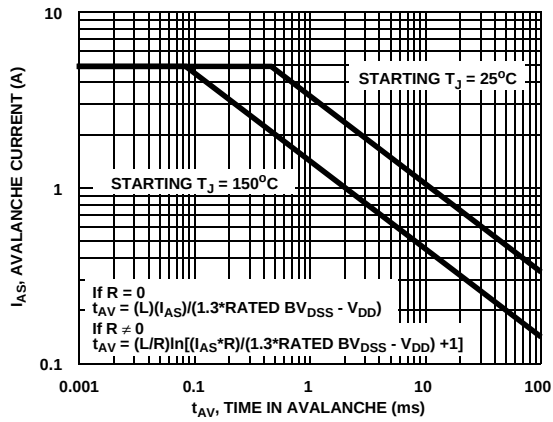


Figure 5. Unclamped Inductive Switching Capability

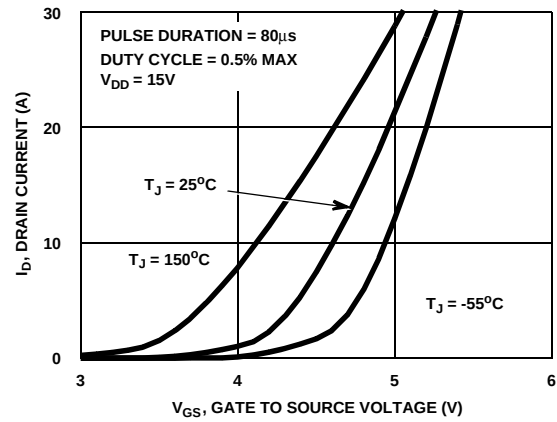


Figure 6. Transfer Characteristics

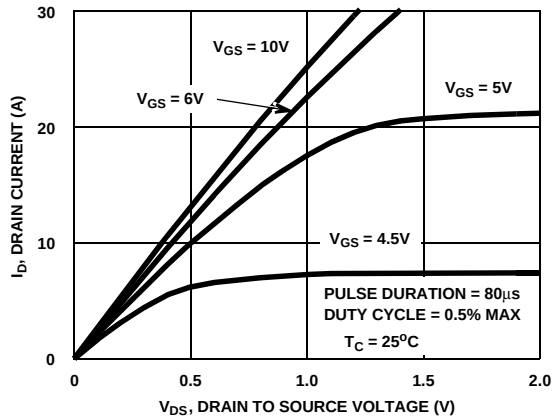


Figure 7. Saturation Characteristics

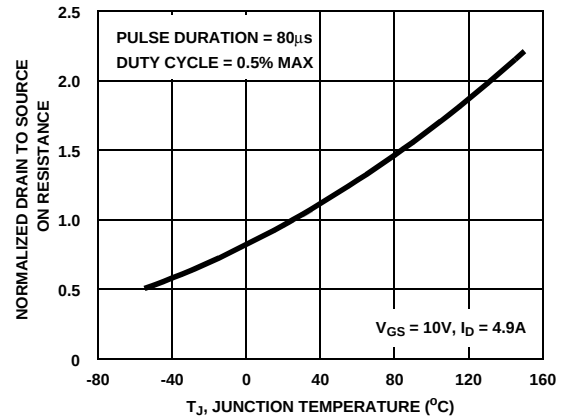


Figure 8. Normalized Drain to Source On Resistance vs Junction Temperature

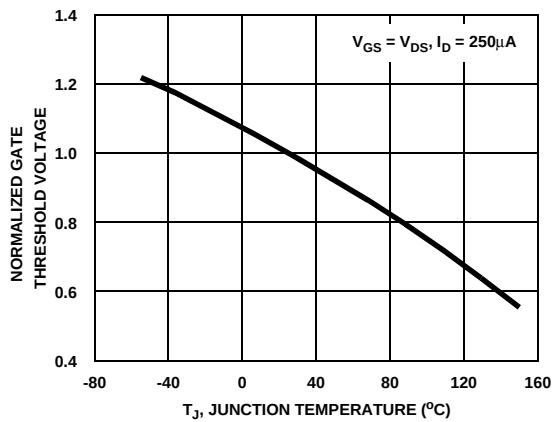


Figure 9. Normalized Gate Threshold Voltage vs Junction Temperature

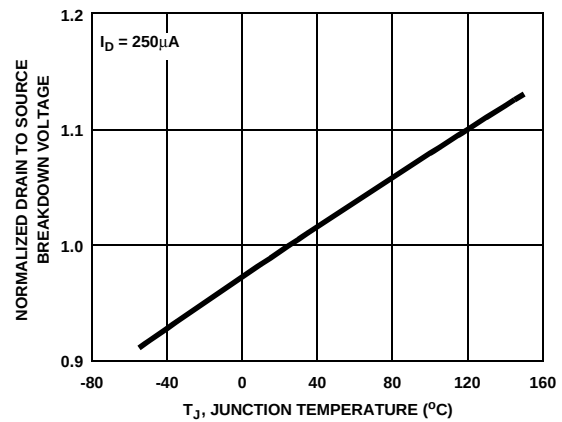


Figure 10. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

Typical Characteristic (Continued)

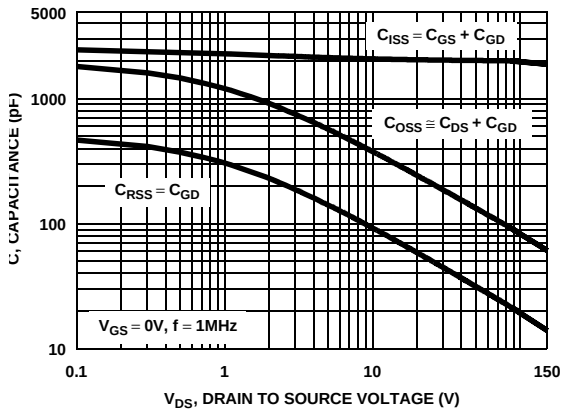


Figure 11. Capacitance vs Drain to Source Voltage

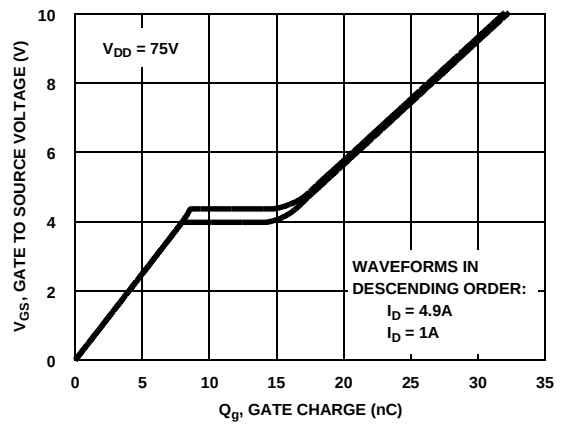


Figure 12. Gate Charge Waveforms for Constant Gate Currents

Test Circuits and Waveforms

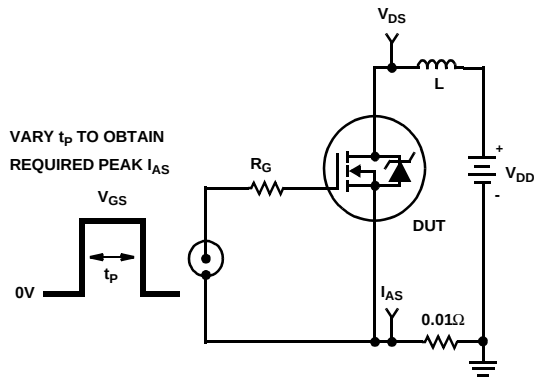


Figure 13. Unclamped Energy Test Circuit

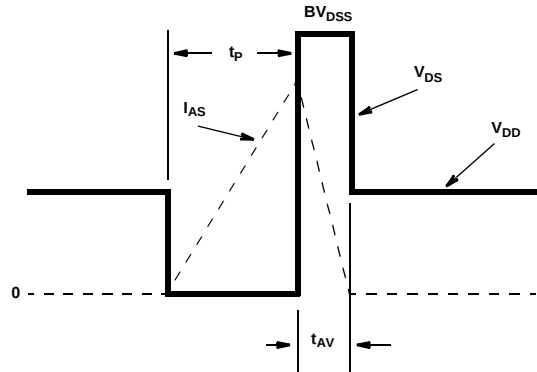


Figure 14. Unclamped Energy Waveforms

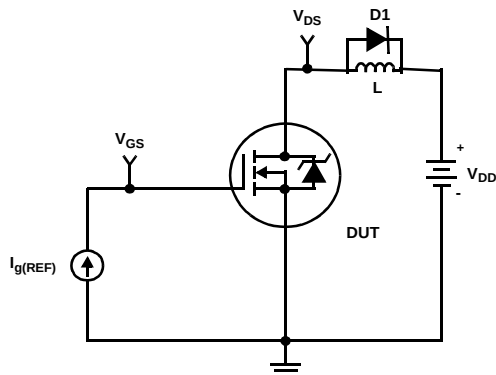


Figure 15. Gate Charge Test Circuit

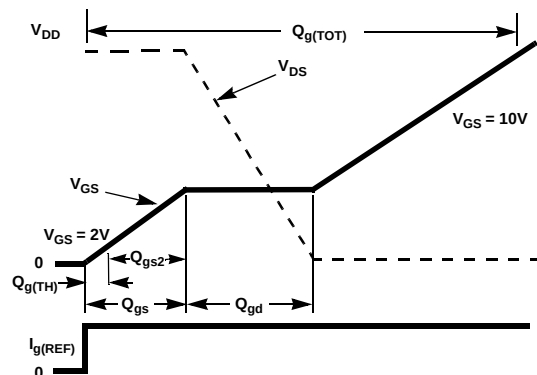


Figure 16. Gate Charge Waveforms

Test Circuits and Waveforms (Continued)

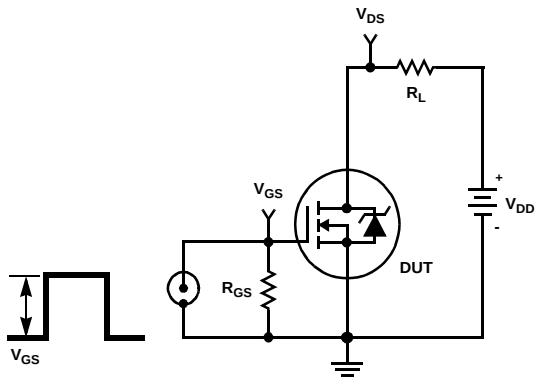


Figure 17. Switching Time Test Circuit

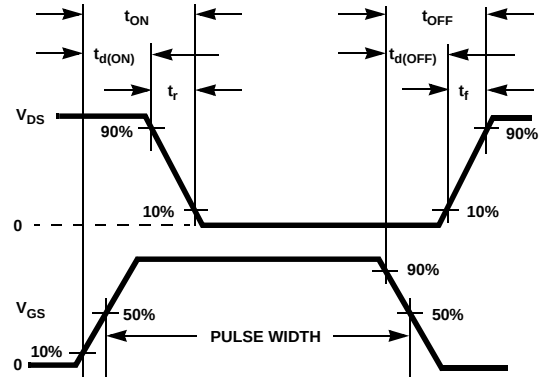


Figure 18. Switching Time Waveforms

Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A ($^{\circ}\text{C}$), and thermal resistance $R_{\theta JA}$ ($^{\circ}\text{C}/\text{W}$) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \quad (\text{EQ. 1})$$

In using surface mount devices such as the SO8 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 19 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually

utilizing the normalized maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 19 or by calculation using Equation 2. The area, in square inches is the top copper area including the gate and source pads.

$$R_{\theta JA} = 64 + \frac{26}{0.23 + \text{Area}} \quad (\text{EQ. 2})$$

The transient thermal impedance ($Z_{\theta JA}$) is also effected by varied top copper board area. Figure 20 shows the effect of copper pad area on single pulse transient thermal impedance. Each trace represents a copper pad area in square inches corresponding to the descending list in the graph. Spice and SABER thermal models are provided for each of the listed pad areas.

Copper pad area has no perceivable effect on transient thermal impedance for pulse widths less than 100ms. For pulse widths less than 100ms the transient thermal impedance is determined by the die and package. Therefore, CTHERM1 through CTHERM5 and RTHERM1 through RTHERM5 remain constant for each of the thermal models. A listing of the model component values is available in Table 1.

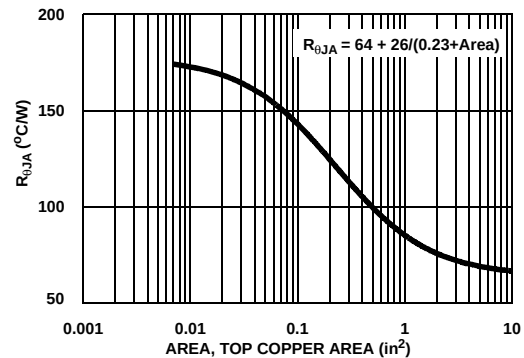


Figure 19. Thermal Resistance vs Mounting Pad Area

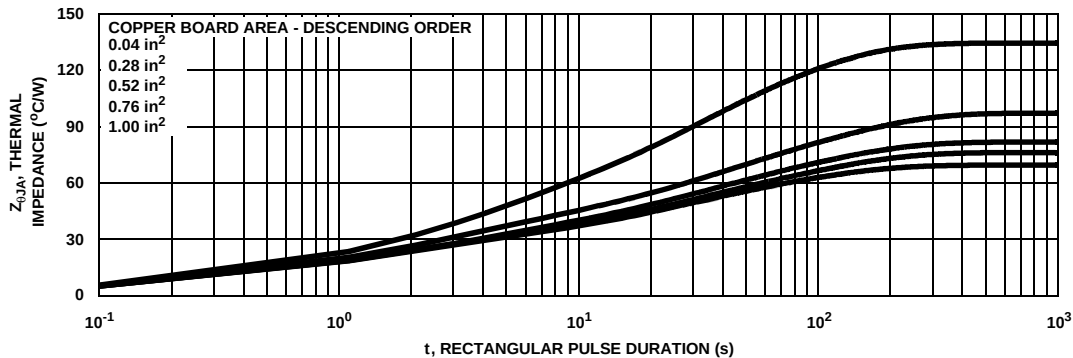


Figure 20. Thermal Impedance vs Mounting Pad Area

PSPICE Electrical Model

.SUBCKT FDS2572 2 1 3 ; rev August 2001

CA 12 8 8e-10

Cb 15 14 8e-10

Cin 6 8 2e-9

Dbody 7 5 DbodyMOD
 Dbreak 5 11 DbreakMOD
 Dplcap 10 5 DplcapMOD

Ebreak 11 7 17 18 157.4
 Eds 14 8 5 8 1
 Egs 13 8 6 8 1
 Esg 6 10 6 8 1
 Evthres 6 21 19 8 1
 Evtemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 5.61e-9
 Ldrain 2 5 1.0e-9
 Lsource 3 7 1.98e-9

RLgate 1 9 56.1
 RLdrain 2 5 10
 RLsource 3 7 19.8

Mstro 16 6 8 8 MstroMOD
 Mmed 16 6 8 8 MmedMOD
 Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1
 Rdrain 50 16 RdrainMOD 2.1e-2
 Rgate 9 20 1.47
 RSLC1 5 51 RSLCMOD 1e-6
 RSLC2 5 50 1e3
 Rsource 8 7 RsourceMOD 1.5e-2
 Rvthres 22 8 RvthresMOD 1
 Rvtemp 18 19 RvtempMOD 1
 S1a 6 12 13 8 S1AMOD
 S1b 13 12 13 8 S1BMOD
 S2a 6 15 14 13 S2AMOD
 S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

ESLC 51 50 VALUE={{(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*65),3))}}

.MODEL DbodyMOD D (IS=4e-11 N=1.131 RS=4.4e-3 TRS1=2e-3 TRS2=1e-6
 + CJO=1.44e-9 M=0.67 TT=7.4e-8 XTI=4.2)

.MODEL DbreakMOD D (RS=0.38 TRS1=2e-3 TRS2=-8.9e-6)

.MODEL DplcapMOD D (CJO=5e-10 IS=1e-30 N=10 M=0.7)

.MODEL MstroMOD NMOS (VTO=4.05 KP=85 IS=1e-30 N=10 TOX=1 L=1u W=1u)

.MODEL MmedMOD NMOS (VTO=3.35 KP=5 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=1.47)

.MODEL MweakMOD NMOS (VTO=2.76 KP=0.05 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=14.7 RS=0.1)

.MODEL RbreakMOD RES (TC1=1.1e-3 TC2=-3e-7)

.MODEL RdrainMOD RES (TC1=1e-2 TC2=3e-5)

.MODEL RSLCMOD RES (TC1=3e-3 TC2=1e-6)

.MODEL RsourceMOD RES (TC1=4.5e-3 TC2=1e-6)

.MODEL RvtempMOD RES (TC1=-5e-3 TC2=2e-6)

.MODEL RvthresMOD RES (TC1=-3e-3 TC2=-1.4e-5)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-10 VOFF=-2)

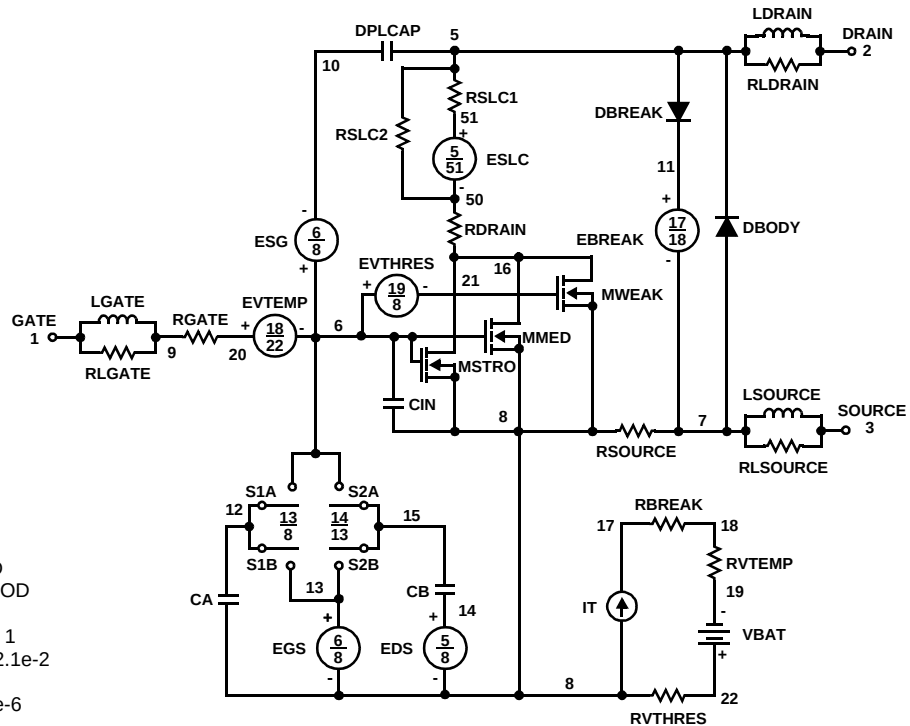
.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2 VOFF=-10)

.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-0.8 VOFF=0.3)

.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.3 VOFF=-0.8)

.ENDS

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.



SPICE Thermal Model

REV August 2001
FDS2572
Copper Area = 1 in²

CTHERM1 TH 8 2.0e-3
CTHERM2 8 7 5.0e-3
CTHERM3 7 6 1.0e-2
CTHERM4 6 5 4.0e-2
CTHERM5 5 4 9.0e-2
CTHERM6 4 3 2.0e-1
CTHERM7 3 2 1
CTHERM8 2 TL 3

RTHERM1 TH 8 1.0e-1
RTHERM2 8 7 5.0e-1
RTHERM3 7 6 1
RTHERM4 6 5 5
RTHERM5 5 4 8
RTHERM6 4 3 12
RTHERM7 3 2 18
RTHERM8 2 TL 25

SABER Thermal Model

Copper Area = 1 in²
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th c2 =2.0e-3
ctherm.ctherm2 c2 c3 =5.0e-3
ctherm.ctherm3 c3 c4 =1.0e-2
ctherm.ctherm4 c4 c5 =4.0e-2
ctherm.ctherm5 c5 c6 =9.0e-2
ctherm.ctherm6 c6 c7 =2.0e-1
ctherm.ctherm7 c7 c8 =1
ctherm.ctherm8 c8 tl =3
}

rtherm.rtherm1 th c2 =1.0e-1
rtherm.rtherm2 c2 c3 =5.0e-1
rtherm.rtherm3 c3 c4 =1
rtherm.rtherm4 c4 c5 =5
rtherm.rtherm5 c5 c6 =8
rtherm.rtherm6 c6 c7 =12
rtherm.rtherm7 c7 c8 =18
rtherm.rtherm8 c8 tl =25
}

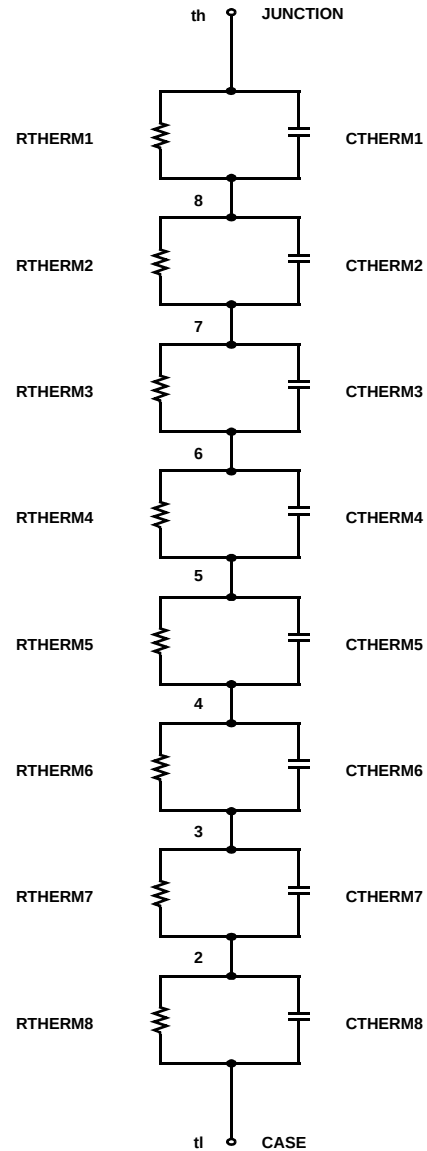
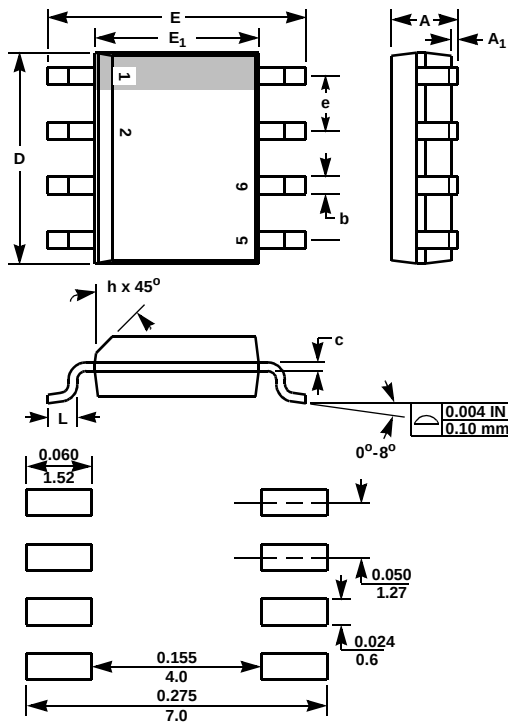


TABLE 1. THERMAL MODELS

COMPONANT	0.04 in ²	0.28 in ²	0.52 in ²	0.76 in ²	1.0 in ²
CTHERM6	1.2e-1	1.5e-1	2.0e-1	2.0e-1	2.0e-1
CTHERM7	0.5	1.0	1.0	1.0	1.0
CTHERM8	1.3	2.8	3.0	3.0	3.0
RTHERM6	26	20	15	13	12
RTHERM7	39	24	21	19	18
RTHERM8	55	38.7	31.3	29.7	25

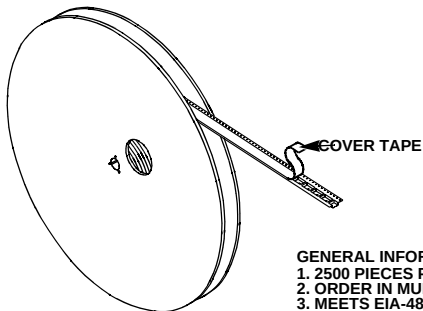
MS-012AA**8 LEAD JEDEC MS-012AA SMALL OUTLINE PLASTIC PACKAGE**

MINIMUM RECOMMENDED FOOTPRINT FOR
SURFACE-MOUNTED APPLICATIONS

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.0532	0.0688	1.35	1.75	-
A ₁	0.004	0.0098	0.10	0.25	-
b	0.013	0.020	0.33	0.51	-
c	0.0075	0.0098	0.19	0.25	-
D	0.189	0.1968	4.80	5.00	2
E	0.2284	0.244	5.80	6.20	-
E ₁	0.1497	0.1574	3.80	4.00	3
e	0.050 BSC		1.27 BSC		-
H	0.0099	0.0196	0.25	0.50	-
L	0.016	0.050	0.40	1.27	4

NOTES:

1. All dimensions are within allowable dimensions of Rev. C of JEDEC MS-012AA outline dated 5-90.
2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.006 inches (0.15mm) per side.
3. Dimension "E₁" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 0.010 inches (0.25mm) per side.
4. "L" is the length of terminal for soldering.
5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
6. Controlling dimension: Millimeter.
7. Revision 8 dated 5-99.

MS-012AA**12mm TAPE AND REEL**

- GENERAL INFORMATION**
1. 2500 PIECES PER REEL.
 2. ORDER IN MULTIPLES OF FULL REELS ONLY.
 3. MEETS EIA-481 REVISION "A" SPECIFICATIONS.

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CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOME™	HiSeC™	PowerTrench [®]	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E ² CMOS™	LittleFET™	QS™	TinyLogic™	
EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SILENT SWITCHER [®]	UltraFET [®]	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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